100V P-Channel MOSFETs

General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-100V	38mΩ	-35A

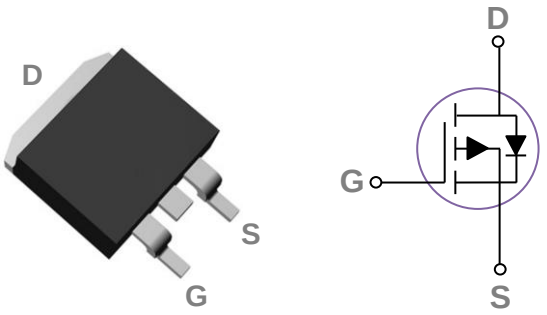
Features

- *-100V,-35A, RDS(ON) 38mΩ@VGS = -10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

Applications

- *Networking*
- *Load Switch*
- *LED applications*

TO263 Pin Configuration



Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	-35	A
	Drain Current – Continuous (T_C=100℃)	-22	A
I_{DM}	Drain Current – Pulsed[1]	-140	A
EAS	Single Pulse Avalanche Energy[2]	180	mJ
IAS	Single Pulse Avalanche Current[2]	-60	A
P_D	Power Dissipation (T_C=25℃)	113	W
	Power Dissipation – Derate above 25℃	0.9	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.1	℃/W

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-80V , V_{GS}=0V , T_J=85℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-15A	---	32	38	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	36	47	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.6	-2.5	V
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-5A	---	21	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=-50V , V_{GS}=-10V , I_D=-20	---	92	140	nC
Q_{gs}	Gate-Source Charge[3,4]		---	13	20	
Q_{gd}	Gate-Drain Charge[3,4]		---	14	20	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=-50V , V_{GS}=-10V , R_G=6Ω , I_D=-20	---	10	15	ns
T_r	Rise Time[3,4]		---	15	25	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	20	30	
T_f	Fall Time[3,4]		---	25	40	
C_{iss}	Input Capacitance	V_{DS}=-50V , V_{GS}=0V , F=1MHz	---	5700	8550	pF
C_{oss}	Output Capacitance		---	160	240	
C_{rss}	Reverse Transfer Capacitance		---	120	180	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-35	A
I_{SM}	Pulsed Source Current		---	---	-70	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V
t_{rr}	Reverse Recovery Time	V_R=-50V, I_S=-10A , di/dt=100A/μs, T_J=25℃	---	55	---	ns
Q_{rr}	Reverse Recovery Charge		---	60	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=-50V,V_{GS}=-10V,L=0.1mH,I_{AS}=-60A.,Starting T_J=25℃
3. The data tested by pulsed , pulse width ≦300us , duty cycle ≦2%.
4. Essentially independent of operating temperature.

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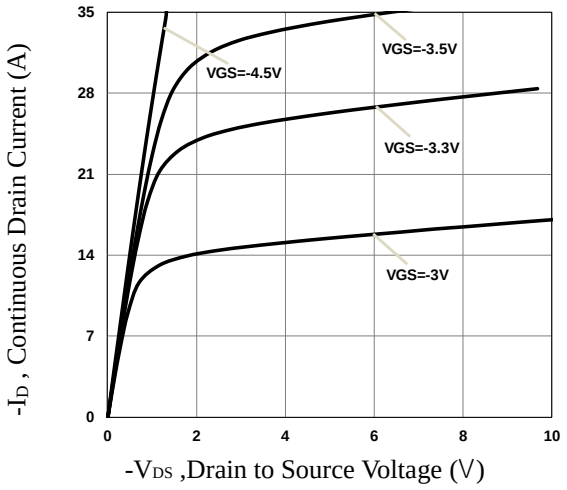

Fig.1 Typical Output Characteristics

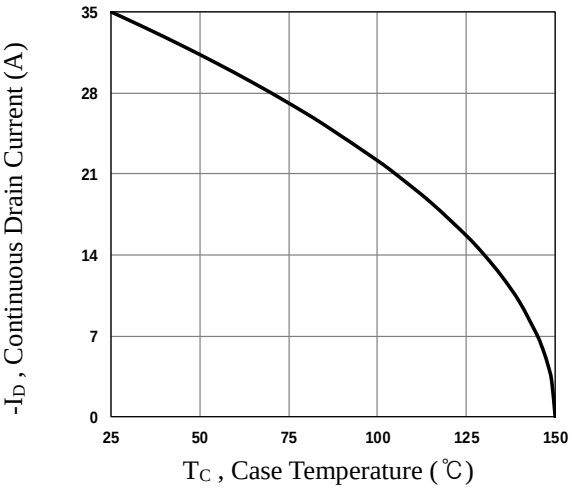

Fig.2 Continuous Drain Current vs. T_C

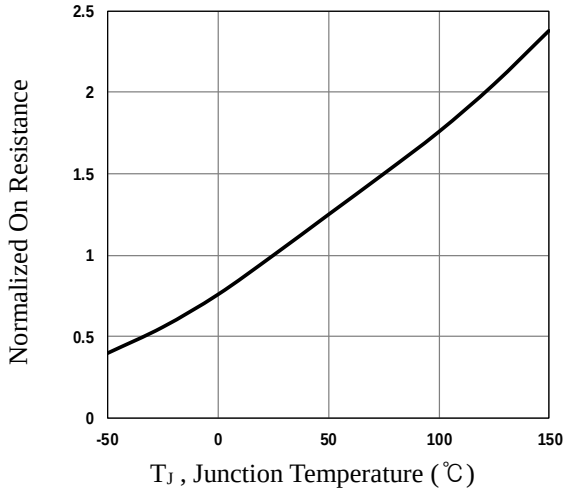

Fig.3 Normalized RDSON vs. T_J

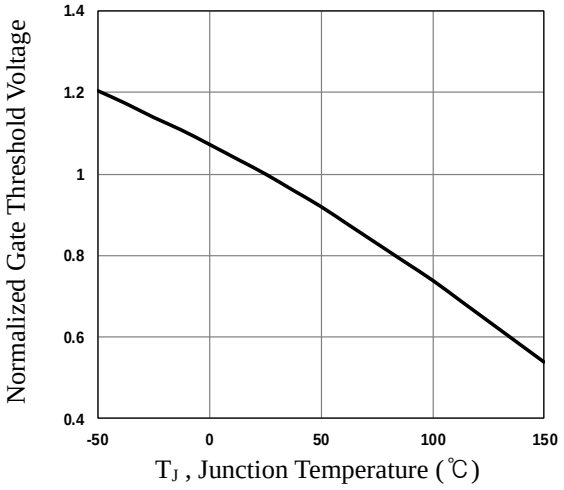

Fig.4 Normalized V_{th} vs. T_J

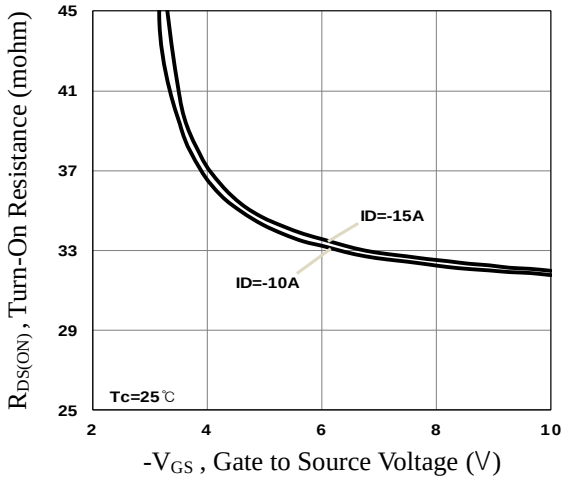

Fig.5 Turn-On Resistance vs. V_{GS}

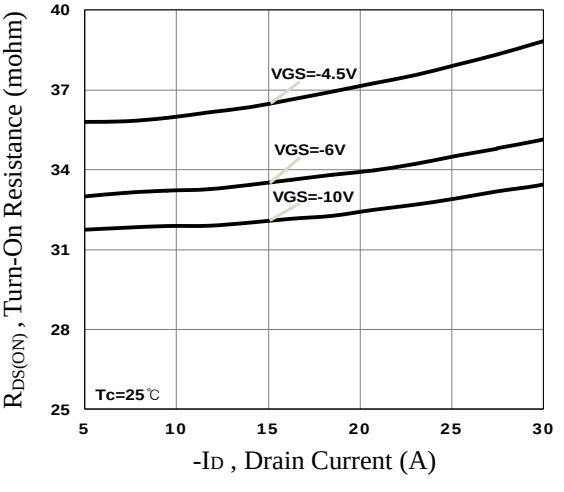

Fig.6 Turn-On Resistance vs. ID

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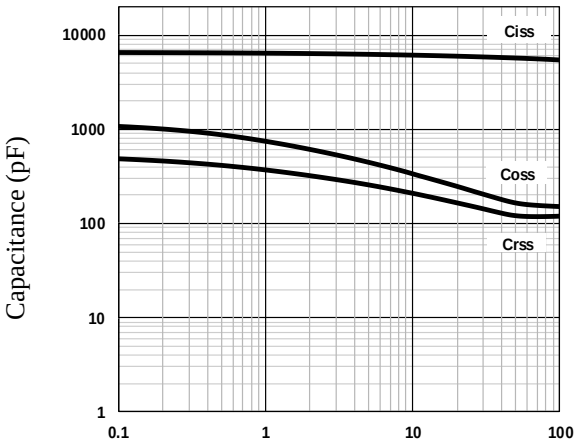
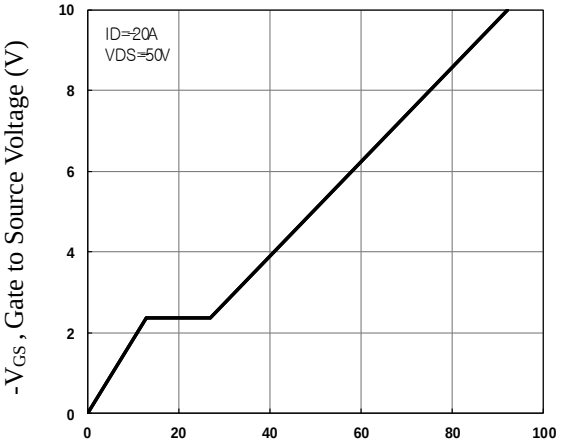


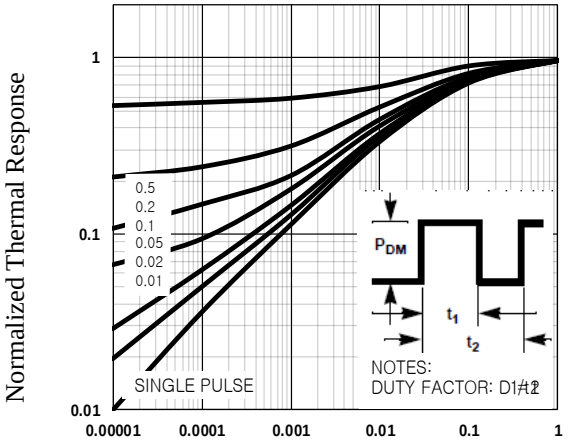
$-V_{DS}$, Drain to Source Voltage (V)

Fig.7 Capacitance Characteristics



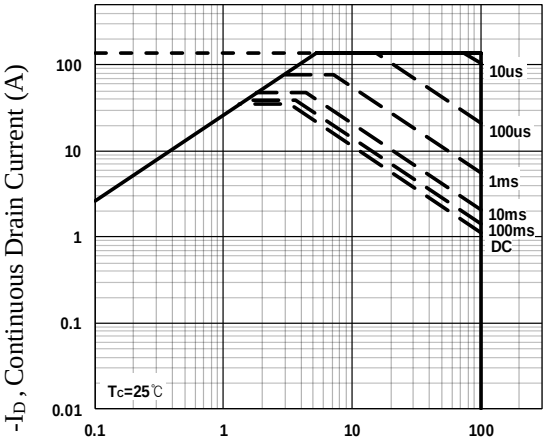
Qg , Gate Charge (nC)

Fig.8 Gate Charge Characteristics



Square Wave Pulse Duration (s)

Fig.9 Normalized Transient Impedance



$-V_{DS}$, Drain to Source Voltage (V)

Fig.10 Maximum Safe Operation Area

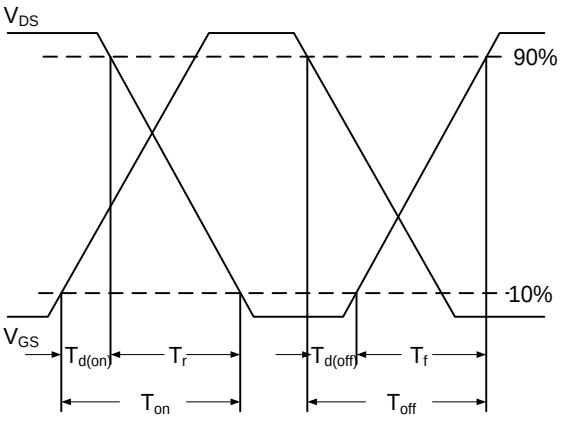


Fig.11 Switching Time Waveform

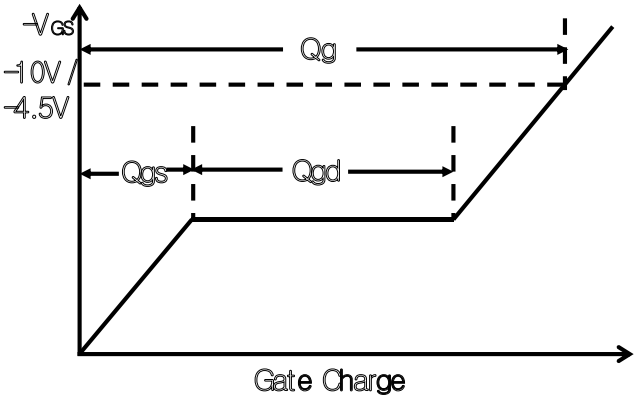


Fig.12 Gate Charge Waveform

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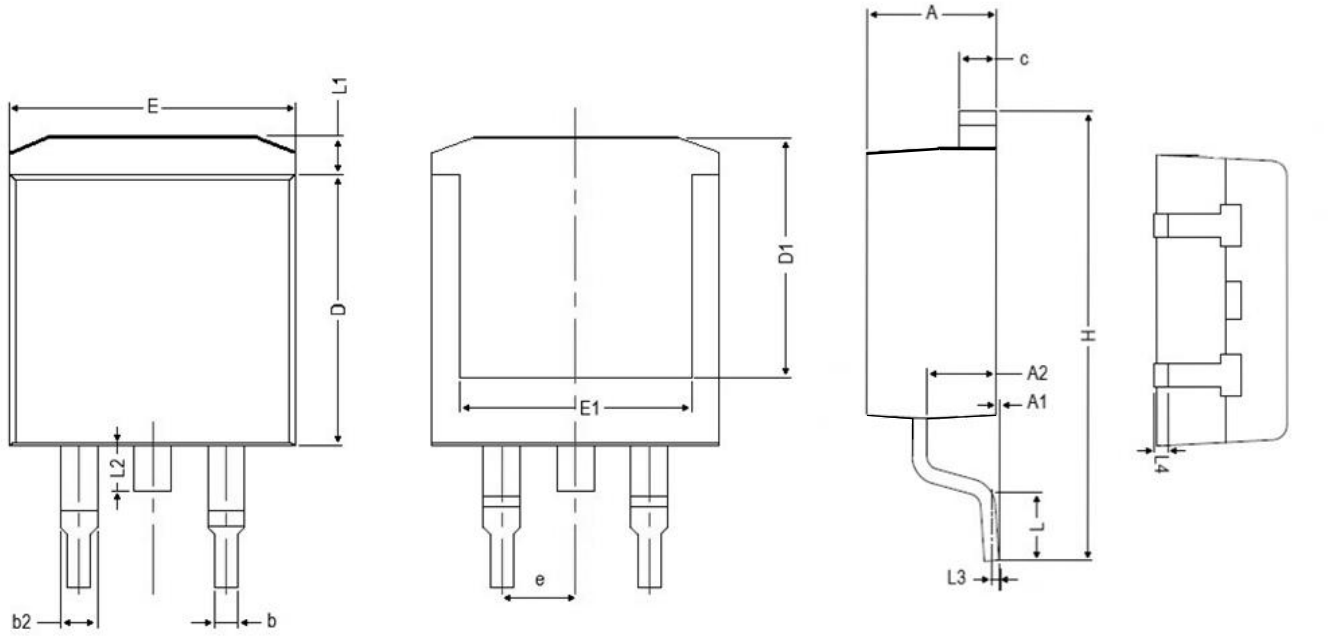
TO263 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	4.850	4.200	0.191	0.165
A1	0.300	0.000	0.012	0.000
A2	2.900	2.200	0.114	0.087
b	0.950	0.700	0.037	0.028
b2	1.700	1.000	0.067	0.039
c	1.450	1.150	0.057	0.045
D	9.500	8.350	0.374	0.329
D1	9.150	6.400	0.360	0.252
E	10.500	9.600	0.413	0.378
E1	8.900	6.850	0.350	0.270
e	2.540 BSC		0.100 BSC	
H	15.900	14.600	0.626	0.575
L	2.800	1.700	0.110	0.067
L1	1.700	1.050	0.067	0.041
L2	2.100	1.300	0.083	0.051
L3	0.250 BSC		0.010 BSC	
L4	0.750	0.200	0.030	0.008